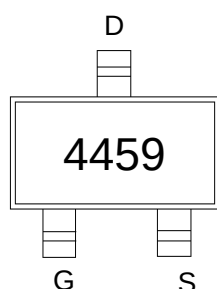


Features

- Trench Power LV MOSFET technology
- High density cell design for Low $R_{DS(ON)}$
- High Speed switching

Application

- Battery protection
- Load switch
- Power management

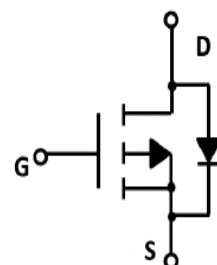
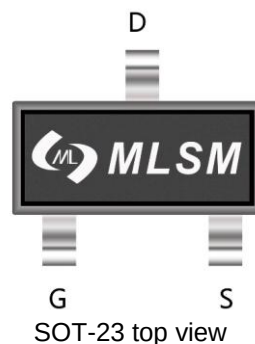


4459: Device code

Marking and pin assignment

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
-30V	35mΩ@-10V	-5A
	55mΩ@-4.5V	



Schematic diagram



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage		-30	V
V_{GS}	Gate-Source Voltage		±20	V
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-50 to 155	°C
I_S	Diode Continuous Forward Current	Tc=25°C	-5	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	Tc=25°C	-20	A
I_D	Continuous Drain Current	Tc=25°C	-5	A
P_D	Maximum Power Dissipation	Tc=25°C	0.35	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		357	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
CJ4459	SOT-23	4459	3,000	45,000	180,000	7"reel

Electrical Characteristics (TJ=25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V	--	--	-1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.4	-2.0	-2.4	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-5A	--	35	46	mΩ
		V _{GS} =-4.5V, I _D =-4A	--	55	72	mΩ
Dynamic Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	--	580	--	pF
C _{OSS}	Output Capacitance		--	98	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	74	--	pF
Q _g	Total Gate Charge	V _{DS} =-15V, I _D =-4.1A, V _{GS} =-10V	--	6.8	--	nC
Q _{gs}	Gate Source Charge		--	1	--	nC
Q _{gd}	Gate Drain Charge		--	1.4	--	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =-15V, I _D =-1A, V _{GS} =-10V, R _G =2.5Ω	--	14	--	nS
t _r	Turn-on Rise Time		--	61	--	nS
t _{d(off)}	Turn-Off Delay Time		--	19	--	nS
t _f	Turn-Off Fall Time		--	10	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	Tj=25℃, Is=-5A	--	--	-1.2	V

Typical Operating Characteristics

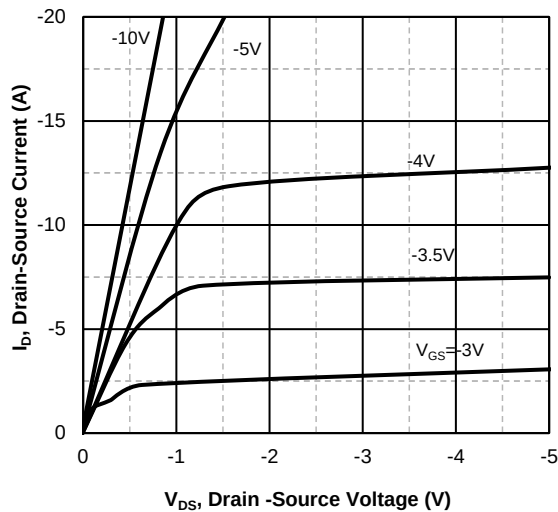


Fig1. Typical Output Characteristics

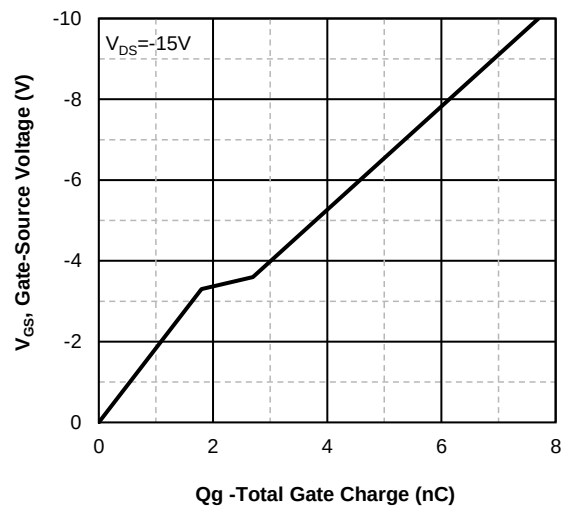


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

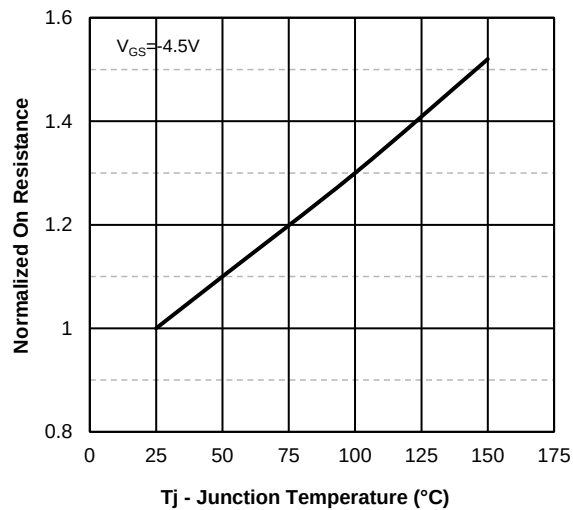


Fig3. Normalized On-Resistance Vs. Temperature

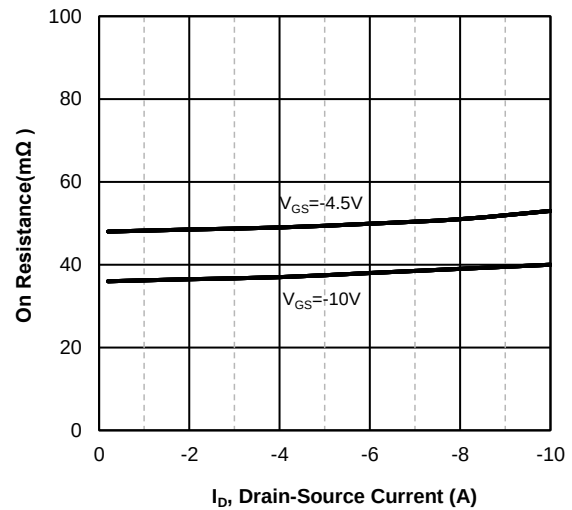


Fig4. On-Resistance Vs. Drain-Source Current

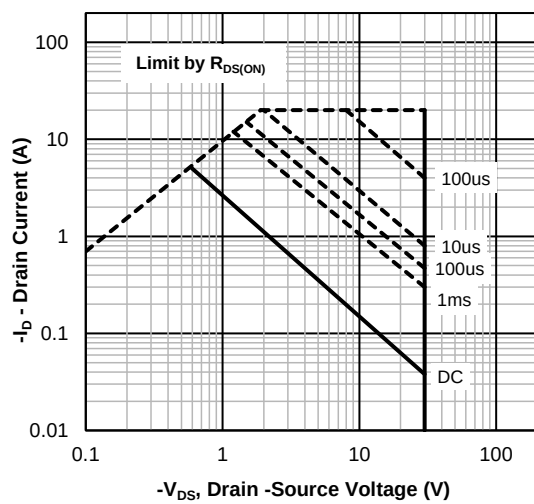


Fig5. Maximum Safe Operating Area

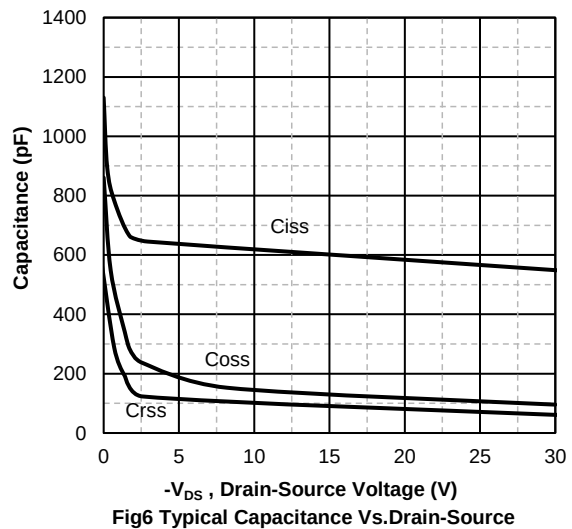
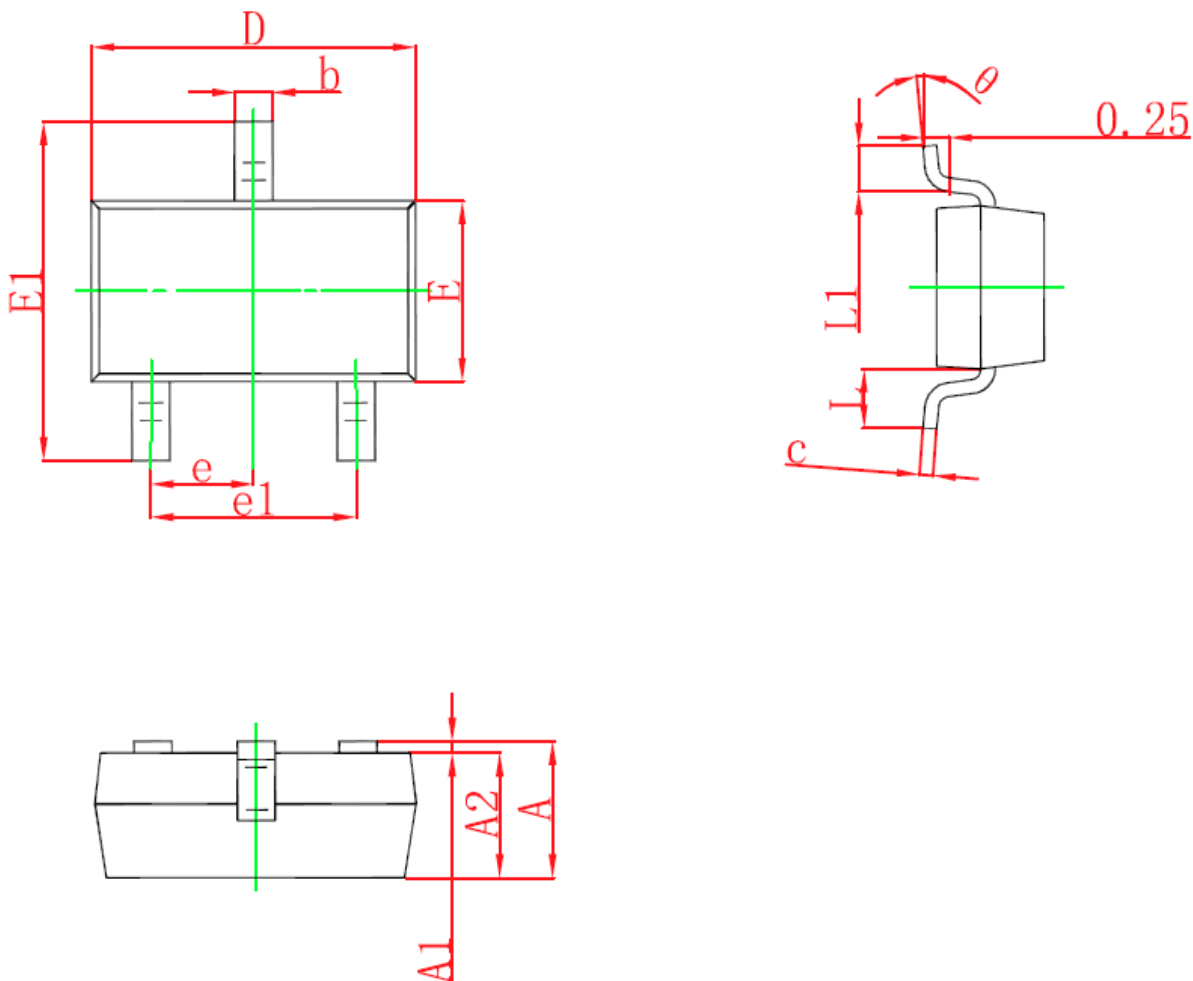


Fig6 Typical Capacitance Vs. Drain-Source

SOT-23 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°